

Description

The PNM8PN20V75A uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge. This device is suitable for use as a load switch or in PWM applications.

MOSFET Product Summary

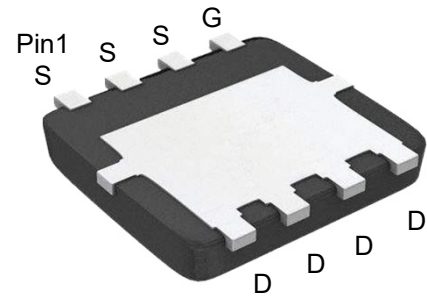
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
20	4.0@ $V_{GS} = 4.5V$	75
	5.0@ $V_{GS} = 2.5V$	

Feature

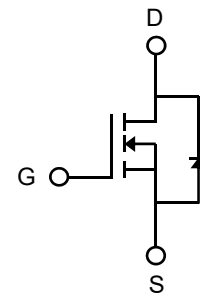
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Applications

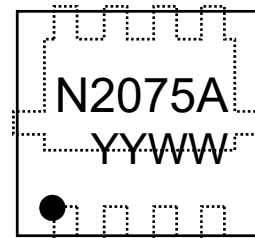
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



Bottom View



Circuit Diagram



Pin1

Marking (Top View)

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous ¹⁾	I_D	$T_C=25^\circ C$	75
		$T_C=100^\circ C$	47
Pulsed Drain Current ²⁾	I_{DM}	300	A
Total Power Dissipation ³⁾	P_D	39.7	W
Avalanche Current ⁴⁾	I_{AS}	47	A
Avalanche Energy ⁴⁾	E_{AS}	110	mJ
Thermal Resistance , Junction-case ⁵⁾	$R_{\theta JC}$	6.5	$^\circ C/W$
Thermal Resistance Junction-to-Ambient ⁵⁾	$R_{\theta JA}$	44.6	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 19.5V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.4	0.6	1.1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 2.5V, I_D = 20A$	-	5.0	9.0	m Ω
		$V_{GS} = 4.5V, I_D = 20A$	-	4.0	5.0	
Dynamic Characteristics⁶⁾						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1.0MHz$	-	2565	-	pF
Output Capacitance	C_{oss}		-	450	-	
Reverse Transfer Capacitance	C_{rss}		-	433	-	
Switching Characteristics⁶⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 15V, V_{GS} = 4.5V,$ $R_G = 3\Omega, I_D = 20A$	-	4.5	-	ns
Turn-on Rise Time	t_r		-	24.9	-	
Turn-Off Delay Time	$t_{d(off)}$		-	197	-	
Turn-Off Fall Time	t_f		-	88	-	
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V,$ $I_D = 20A$	-	37	-	nC
Gate-Source Charge	Q_{gs}		-	4.5	-	
Gate-Drain Charge	Q_{gd}		-	10	-	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	1.9	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 20A$	-	0.85	1.3	V

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. This single-pulse measurement was taken under the following condition ($L=100uH, V_{GS}=10V, V_{DS}=35V$)while it's value is limited by $T_{J_Max}=150^\circ C$.
5. Device mounted on infinite heatsink.
6. Guaranteed by design, not subject to production.

Typical Characteristics

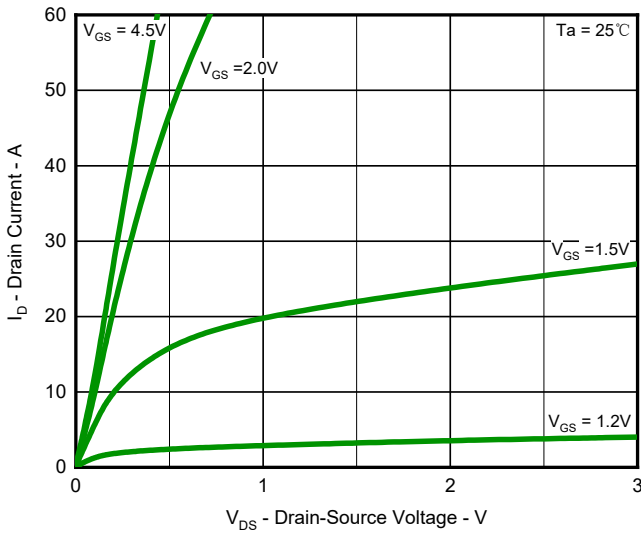


Fig.1 Output Characteristics

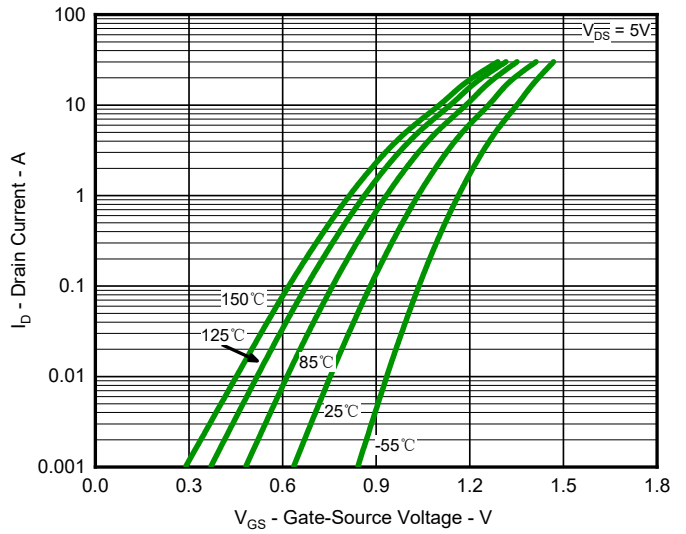


Fig.2 Typical Transfer Characteristic

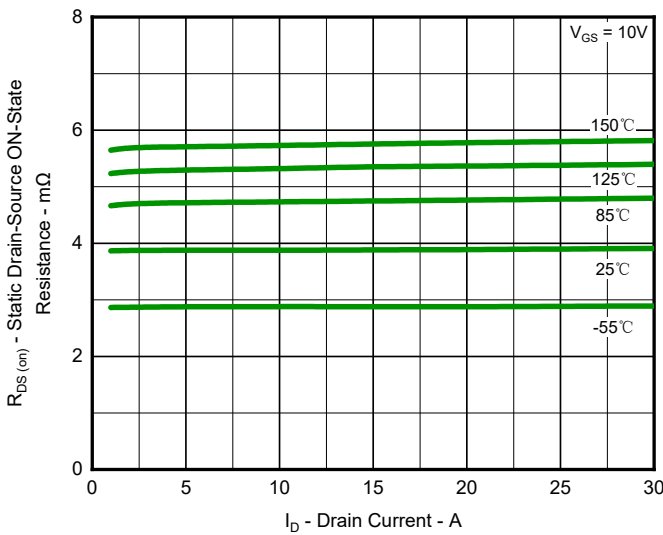


Fig.3 Typical On-Resistance vs Drain Current and Temperature

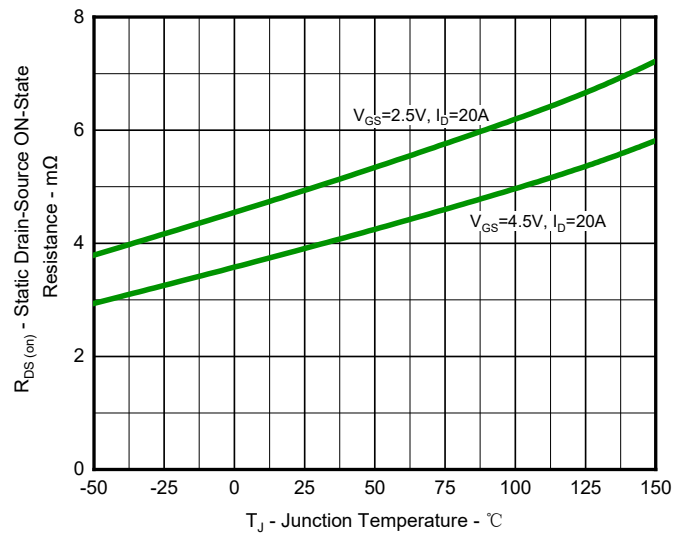


Fig.4 On-Resistance Variation with Temperature

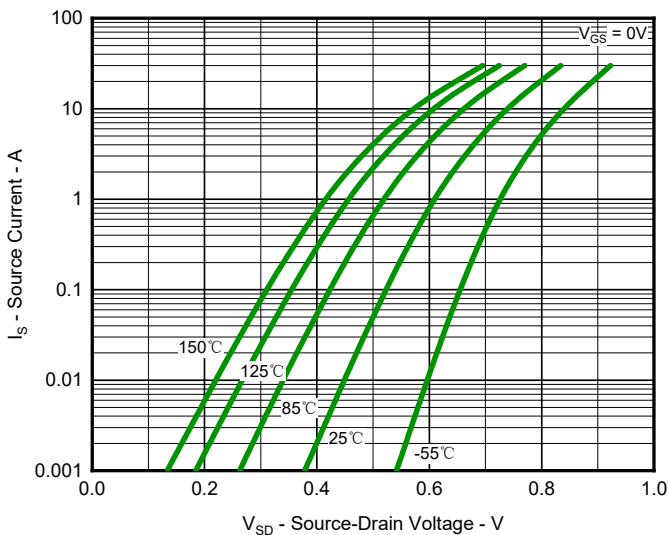


Fig.5 Diode Forward Voltage vs. Current

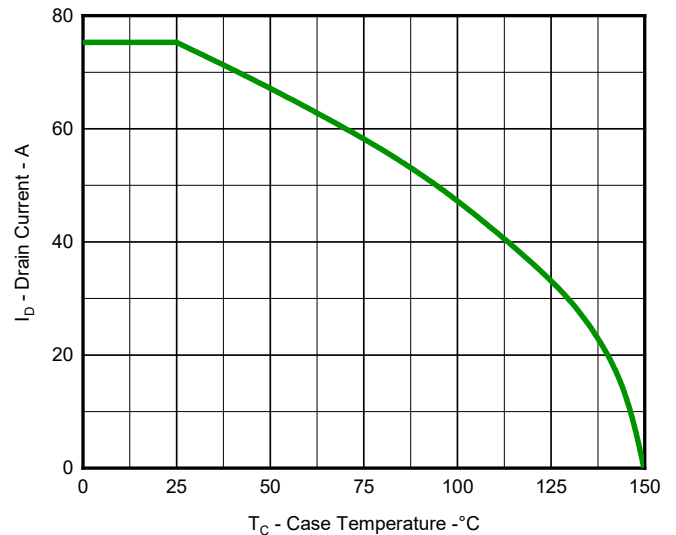


Fig.6 Maximum Drain Current vs. Case Temperature

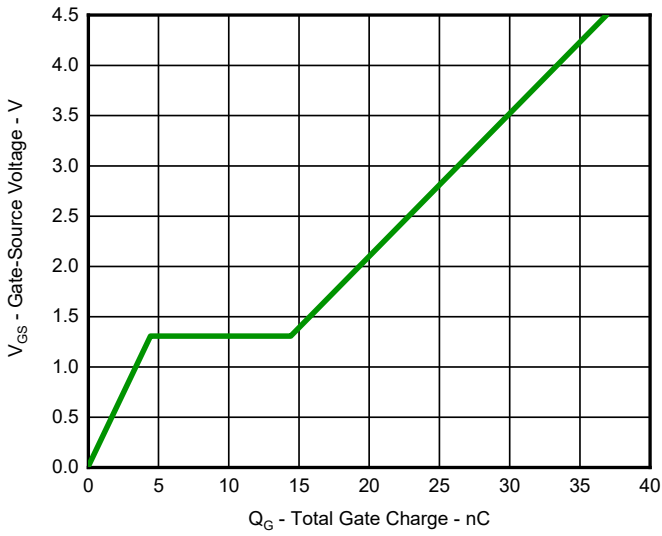


Fig.7 Gate Charge Characteristics

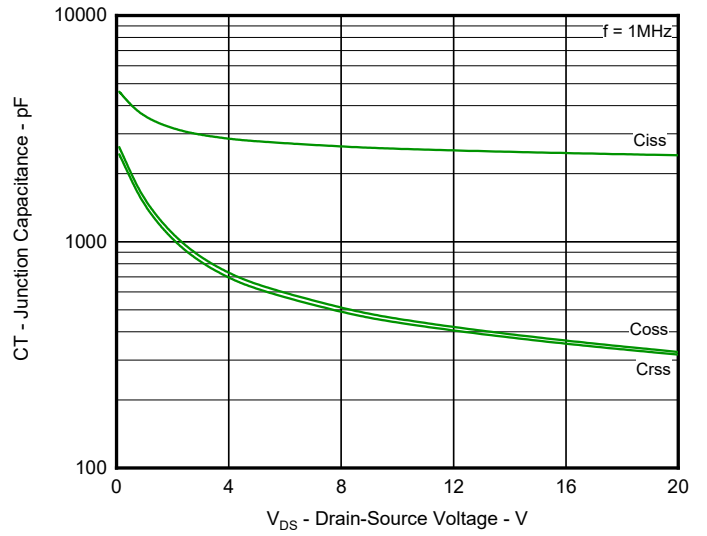


Fig.8 Typical Junction Capacitance

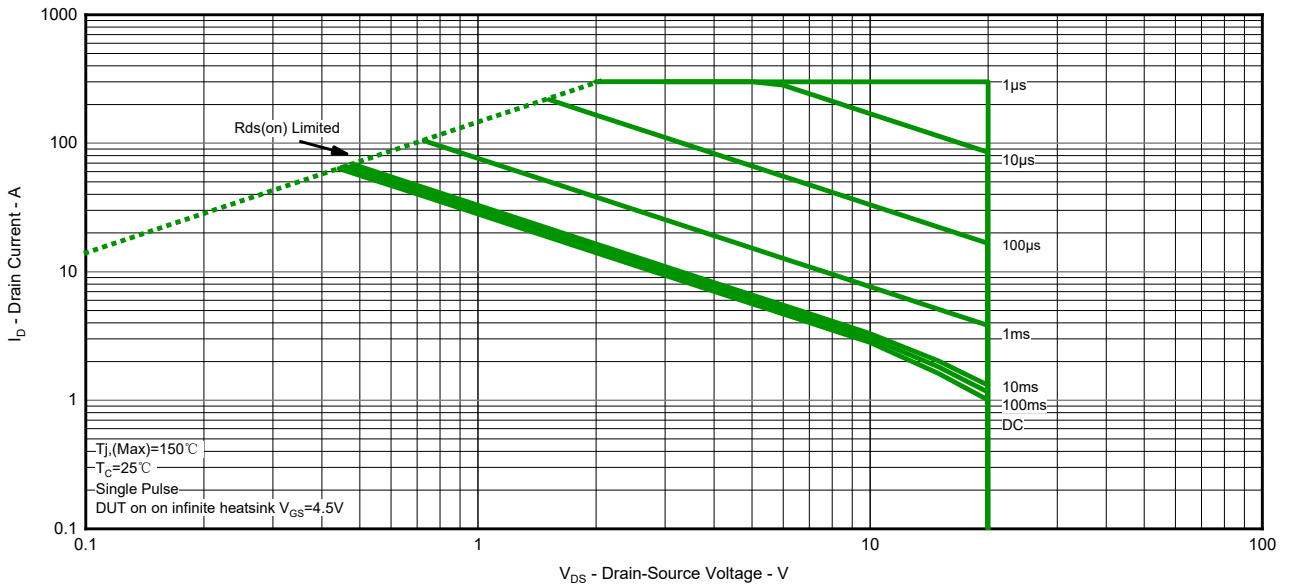


Fig.9 Safe Operation Area

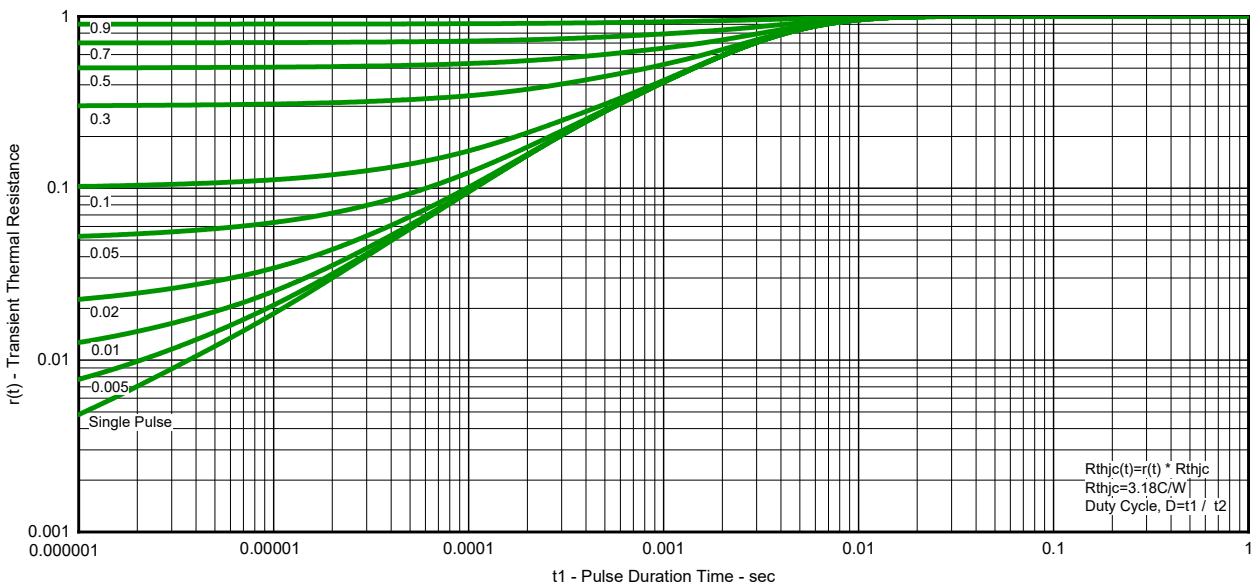
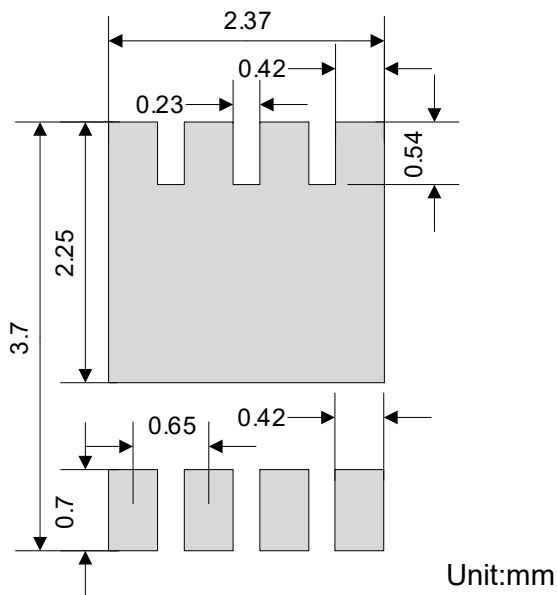
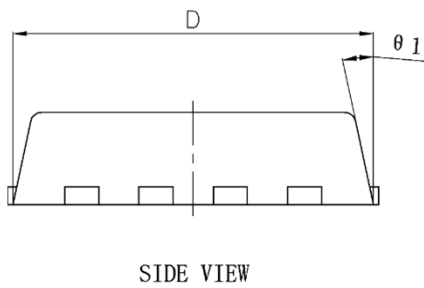
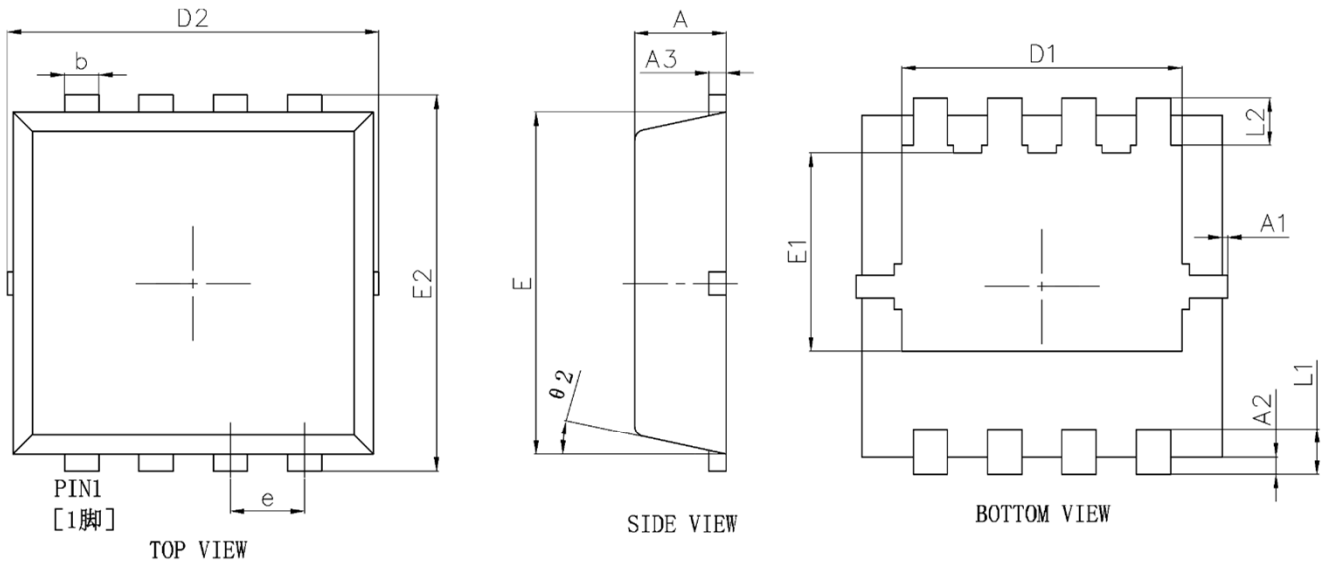


Fig.10 Transient Thermal Resistance

Product Dimension (DFN3333-8L)



Suggested PCB Layout

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.75	0.85	0.030	0.033
A1	0.00	0.10	0.000	0.004
A2	0.10	0.20	0.004	0.008
A3	0.152 Ref.		0.006 Ref.	
D	3.05	3.25	0.120	0.128
D1	2.35	2.55	0.093	0.100
D2	3.20	3.40	0.126	0.134
E	2.90	3.10	0.114	0.122
E1	1.635	1.835	0.064	0.072
E2	3.15	3.35	0.124	0.132
b	0.20	0.40	0.008	0.016
e	0.625	0.675	0.025	0.027
L1	0.35	0.45	0.014	0.018
L2	0.365	0.465	0.014	0.018
θ1	10°	14°	10°	14°
θ2	10°	14°	10°	14°

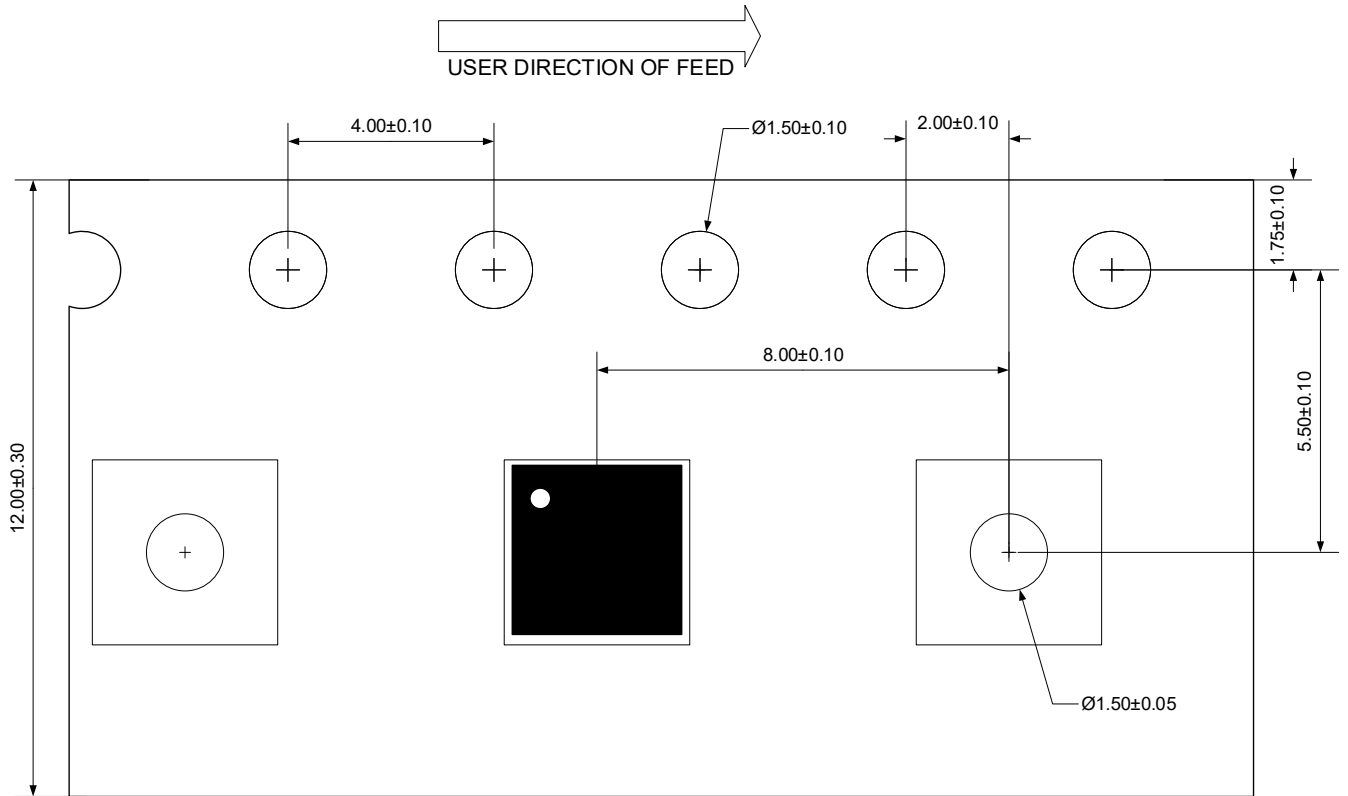
N-Channel MOSFET

PNM8PN20V75A

Ordering Information


Device	Package	Reel	Shipping
PNM8PN20V75A	DFN3333-8L(Pb-Free)	13"	5000 / Tape & Reel

Load With Information



Unit:mm


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